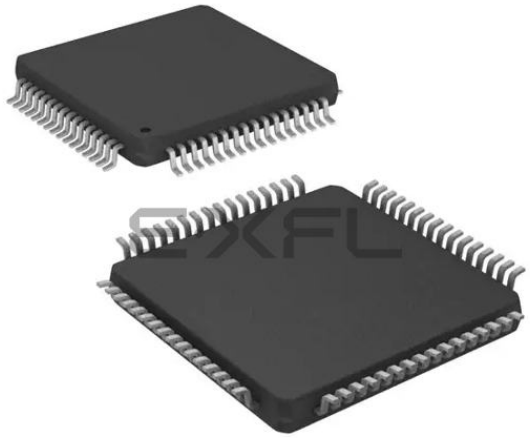

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	AVR
Core Size	8/16-Bit
Speed	32MHz
Connectivity	I²C, IrDA, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, DMA, POR, PWM, WDT
Number of I/O	50
Program Memory Size	256KB (128K x 16)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	64-TQFP
Supplier Device Package	64-TQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/atxmega256a3u-anr

3. For packaging information, see "Packaging information" on page 71.
4. Tape and Reel.

Package Type	
64A	64-lead, 14 x 14mm body size, 1.0mm body thickness, 0.8mm lead pitch, thin profile plastic quad flat package (TQFP)
64M2	64-pad, 9 x 9 x 1.0mm body, lead pitch 0.50mm, 7.65mm exposed pad, quad flat no-lead package (QFN)

Typical Applications

Industrial control	Climate control	Low power battery applications
Factory automation	RF and ZigBee®	Power tools
Building control	USB connectivity	HVAC
Board control	Sensor control	Utility metering
White goods	Optical	Medical applications

6. AVR CPU

6.1 Features

- 8/16-bit, high-performance Atmel AVR RISC CPU
  - 142 instructions
  - Hardware multiplier
- 32x8-bit registers directly connected to the ALU
- Stack in RAM
- Stack pointer accessible in I/O memory space
- Direct addressing of up to 16MB of program memory and 16MB of data memory
- True 16/24-bit access to 16/24-bit I/O registers
- Efficient support for 8-, 16-, and 32-bit arithmetic
- Configuration change protection of system-critical features

6.2 Overview

All Atmel AVR XMEGA devices use the 8/16-bit AVR CPU. The main function of the CPU is to execute the code and perform all calculations. The CPU is able to access memories, perform calculations, control peripherals, and execute the program in the flash memory. Interrupt handling is described in a separate section, refer to "Interrupts and Programmable Multilevel Interrupt Controller" on page 30.

6.3 Architectural Overview

In order to maximize performance and parallelism, the AVR CPU uses a Harvard architecture with separate memories and buses for program and data. Instructions in the program memory are executed with single-level pipelining. While one instruction is being executed, the next instruction is pre-fetched from the program memory. This enables instructions to be executed on every clock cycle. For details of all AVR instructions, refer to http://www.atmel.com/avr.

7.3 Flash Program Memory

The Atmel AVR XMEGA devices contain on-chip, in-system reprogrammable flash memory for program storage. The flash memory can be accessed for read and write from an external programmer through the PDI or from application software running in the device.

All AVR CPU instructions are 16 or 32 bits wide, and each flash location is 16 bits wide. The flash memory is organized in two main sections, the application section and the boot loader section. The sizes of the different sections are fixed, but device-dependent. These two sections have separate lock bits, and can have different levels of protection. The store program memory (SPM) instruction, which is used to write to the flash from the application software, will only operate when executed from the boot loader section.

The application section contains an application table section with separate lock settings. This enables safe storage of nonvolatile data in the program memory.

Table 7-1. Flash Program Memory (Hexadecimal address).

Word Address								
ATxmega256A3U		ATxmega192A3U		ATxmega128A3U		ATxmega64A3U		
0		0		0		0		Application Section (256K/192K/128K/64K)
								...
1EFFF	/	16FFF	/	37FF	/	77FF		
1F000	/	17000	/	EFFF	/	7800		Application Table Section (8K/8K/8K/4K)
1FFFF	/	17FFF	/	F000	/	7FFF		
20000	/	18000	/	10000	/	8000		Boot Section (8K/8K/8K/4K)
20FFF	/	18FFF	/	10FFF	/	87FF		

7.3.1 Application Section

The Application section is the section of the flash that is used for storing the executable application code. The protection level for the application section can be selected by the boot lock bits for this section. The application section can not store any boot loader code since the SPM instruction cannot be executed from the application section.

7.3.2 Application Table Section

The application table section is a part of the application section of the flash memory that can be used for storing data. The size is identical to the boot loader section. The protection level for the application table section can be selected by the boot lock bits for this section. The possibilities for different protection levels on the application section and the application table section enable safe parameter storage in the program memory. If this section is not used for data, application code can reside here.

7.3.3 Boot Loader Section

While the application section is used for storing the application code, the boot loader software must be located in the boot loader section because the SPM instruction can only initiate programming when executing from this section. The SPM instruction can access the entire flash, including the boot loader section itself. The protection level for the boot loader section can be selected by the boot loader lock bits. If this section is not used for boot loader software, application code can be stored here.

36.3.3 Current consumption

Table 36-68. Current consumption for active mode and sleep modes.

Symbol	Parameter	Condition		Min.	Typ.	Max.	Units
I_{CC}	Active Power consumption [1]	32kHz, Ext. Clk	V_{CC} = 1.8V		60		µA
			V_{CC} = 3.0V		140		
		1MHz, Ext. Clk	V_{CC} = 1.8V		260		
			V_{CC} = 3.0V		600		
		2MHz, Ext. Clk	V_{CC} = 1.8V		510	600	
			V_{CC} = 3.0V		1.1	1.5	mA
		32MHz, Ext. Clk			10.6	15	
	Idle Power consumption [1]	32kHz, Ext. Clk	V_{CC} = 1.8V		4.3		µA
			V_{CC} = 3.0V		4.8		
		1MHz, Ext. Clk	V_{CC} = 1.8V		78		
			V_{CC} = 3.0V		150		
		2MHz, Ext. Clk	V_{CC} = 1.8V		150	350	
			V_{CC} = 3.0V		290	600	
		32MHz, Ext. Clk			4.7	7.0	mA
	Power-down power consumption	T = 25°C	V_{CC} = 3.0V		0.1	1.0	µA
		T = 85°C			1.8	5.0	
		T = 105°C			6.5	17	
		WDT and Sampled BOD enabled, T = 25°C	V_{CC} = 3.0V		1.3	3.0	
		WDT and Sampled BOD enabled, T = 85°C			3.1	7.0	
		WDT and Sampled BOD enabled, T = 105°C			7.3	20	
	Power-save power consumption [2]	RTC from ULP clock, WDT and sampled BOD enabled, T = 25°C	V_{CC} = 1.8V		1.2		µA
			V_{CC} = 3.0V		1.3		
		RTC from 1.024kHz low power 32.768kHz TOSC, T = 25°C	V_{CC} = 1.8V		0.6	2	
			V_{CC} = 3.0V		0.7	2	
		RTC from low power 32.768kHz TOSC, T = 25°C	V_{CC} = 1.8V		0.8	3	
			V_{CC} = 3.0V		1.0	3	
	Reset power consumption	Current through $\overline{RESET}$ pin substracted	V_{CC} = 3.0V		250		µA

Notes:
1. All Power Reduction Registers set.
2. Maximum limits are based on characterization, and not tested in production.

Symbol	Parameter	Condition		Min.	Typ.	Max.	Units
	Offset Error, input referred	1x gain, normal mode			-2		mV
		8x gain, normal mode			-5		
		64x gain, normal mode			-4		
	Noise	1x gain, normal mode	V_{CC} = 3.6V Ext. V_{REF}		0.5		mV rms
		8x gain, normal mode			1.5		
		64x gain, normal mode			11		

Note: 1. Maximum numbers are based on characterisation and not tested in production, and valid for 5% to 95% input voltage range.

36.3.7 DAC Characteristics

Table 36-76. Power supply, reference and output range.

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
AV_{CC}	Analog supply voltage		V_{CC}- 0.3		V_{CC}+ 0.3	
AV_{REF}	External reference voltage		1.0		V_{CC}- 0.6	V
$R_{channel}$	DC output impedance				50	Ω
	Linear output voltage range		0.15		AV_{CC}-0.15	V
R_{AREF}	Reference input resistance			>10		MΩ
CAREF	Reference input capacitance	Static load		7		pF
	Minimum Resistance load		1			kΩ
	Maximum capacitance load				100	pF
		1000Ω serial resistance			1	nF
	Output sink/source	Operating within accuracy specification			AV_{CC}/1000	mA
		Safe operation			10	

Table 36-77. Clock and timing.

Symbol	Parameter	Condition		Min.	Typ.	Max.	Units
f_{DAC}	Conversion rate	C_{load}=100pF, maximum step size	Normal mode	0		1000	ksps
			Low power mode	0		500	

Table 36-78. Accuracy characteristics.

Symbol	Parameter	Condition		Min.	Typ.	Max.	Units
RES	Input Resolution					12	Bits
INL [(1)]	Integral non-linearity	V_{REF}= Ext 1.0V	V_{CC} = 1.6V		±2.0	±3	lsb
			V_{CC} = 3.6V		±1.5	±2.5	
		V_{REF}=AV_{CC}	V_{CC} = 1.6V		±2.0	±4	
			V_{CC} = 3.6V		±1.5	±4	
		V_{REF}=INT1V	V_{CC} = 1.6V		±5.0		
			V_{CC} = 3.6V		±5.0		
DNL [(1)]	Differential non-linearity	V_{REF}=Ext 1.0V	V_{CC} = 1.6V		±1.5	3	lsb
			V_{CC} = 3.6V		±0.6	1.5	
		V_{REF}=AV_{CC}	V_{CC} = 1.6V		±1.0	3.5	
			V_{CC} = 3.6V		±0.6	1.5	
		V_{REF}=INT1V	V_{CC} = 1.6V		±4.5		
			V_{CC} = 3.6V		±4.5		
	Gain error	After calibration			<4		lsb
	Gain calibration step size				4		lsb
	Gain calibration drift	V_{REF}= Ext 1.0V			<0.2		mV/K
	Offset error	After calibration			<1		lsb
	Offset calibration step size				1		

Note: 1. Maximum numbers are based on characterisation and not tested in production, and valid for 5% to 95% output voltage range.

36.3.8 Analog Comparator Characteristics

Table 36-79. Analog Comparator characteristics.

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
V_{off}	Input Offset Voltage			<±10		mV
I_{lk}	Input Leakage Current			<1		nA
	Input voltage range		-0.1		AV_{CC}	V
	AC startup time			100		µs
V_{hys1}	Hysteresis, None			0		mV
V_{hys2}	Hysteresis, Small	mode = High Speed (HS)		13		mV
		mode = Low Power (LP)		30		
V_{hys3}	Hysteresis, Large	mode = HS		30		mV
		mode = LP		60		

Symbol	Parameter	Condition		Min.	Typ.	Max.	Units
t_{delay}	Propagation delay	V_{CC} = 3.0V, T= 85°C	mode = HS		30	90	ns
		mode = HS			30		
		V_{CC} = 3.0V, T= 85°C	mode = LP		130	500	
		mode = LP			130		
	64-Level Voltage Scaler	Integral non-linearity (INL)			0.3	0.5	lsb

36.3.9 Bandgap and Internal 1.0V Reference Characteristics

Table 36-80. Bandgap and Internal 1.0V reference characteristics.

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
	Startup time	As reference for ADC or DAC	1 Clk_{PER} + 2.5µs			µs
		As input voltage to ADC and AC		1.5		
	Bandgap voltage			1.1		V
INT1V	Internal 1.00V reference	T= 85°C, after calibration	0.99	1	1.01	mV
	Variation over voltage and temperature	Relative to T= 85°C, V_{CC} = 3.0V		±1.0		%

36.3.10 Brownout Detection Characteristics

Table 36-81. Brownout detection characteristics.

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
V_{BOT}	BOD level 0 falling V_{CC}		1.60	1.62	1.72	V
	BOD level 1 falling V_{CC}			1.8		
	BOD level 2 falling V_{CC}			2.0		
	BOD level 3 falling V_{CC}			2.2		
	BOD level 4 falling V_{CC}			2.4		
	BOD level 5 falling V_{CC}			2.6		
	BOD level 6 falling V_{CC}			2.8		
	BOD level 7 falling V_{CC}			3.0		
t_{BOD}	Detection time	Continuous mode		0.4		µs
		Sampled mode		1000		
V_{HYST}	Hysteresis			1.6		%

Table 36-85. Programming time.

Symbol	Parameter	Condition	Min.	Typ. [1]	Max.	Units
	Chip Erase	192KB Flash, EEPROM [2] and SRAM Erase		90		ms
	Application Erase	Section erase		6		ms
	Flash	Page Erase		4		ms
		Page Write		4		
		Atomic Page Erase and Write		8		
	EEPROM	Page Erase		4		ms
		Page Write		4		
		Atomic Page Erase and Write		8		

Notes: 1. Programming is timed from the 2MHz internal oscillator.
2. EEPROM is not erased if the EESAVE fuse is programmed.

36.3.14 Clock and Oscillator Characteristics

36.3.14.1 Calibrated 32.768kHz Internal Oscillator characteristics

Table 36-86. 32.768kHz internal oscillator characteristics.

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
	Frequency			32.768		kHz
	Factory calibration accuracy	T = 85°C, V_{CC} = 3.0V	-0.5		0.5	%
	User calibration accuracy		-0.5		0.5	%

36.3.14.2 Calibrated 2MHz RC Internal Oscillator characteristics

Table 36-87. 2MHz internal oscillator characteristics.

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
	Frequency range	DFLL can tune to this frequency over voltage and temperature	1.8		2.2	MHz
	Factory calibrated frequency			2.0		MHz
	Factory calibration accuracy	T = 85°C, V_{CC}= 3.0V	-1.5		1.5	%
	User calibration accuracy		-0.2		0.2	%
	DFLL calibration stepsize			0.22		%

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
$t_{SU;STA}$	Set-up time for a repeated START condition	$f_{SCL} \leq 100kHz$	4.7			µs
		$f_{SCL} > 100kHz$	0.6			
$t_{HD;DAT}$	Data hold time	$f_{SCL} \leq 100kHz$	0		3.45	µs
		$f_{SCL} > 100kHz$	0		0.9	
$t_{SU;DAT}$	Data setup time	$f_{SCL} \leq 100kHz$	250			ns
		$f_{SCL} > 100kHz$	100			
$t_{SU;STO}$	Setup time for STOP condition	$f_{SCL} \leq 100kHz$	4.0			µs
		$f_{SCL} > 100kHz$	0.6			
t_{BUF}	Bus free time between a STOP and START condition	$f_{SCL} \leq 100kHz$	4.7			µs
		$f_{SCL} > 100kHz$	1.3			

Notes:
1. Required only for $f_{SCL} > 100kHz$.
2. C_b = Capacitance of one bus line in pF.
3. f_{PER} = Peripheral clock frequency.

Symbol	Parameter	Condition		Min.	Typ.	Max.	Units
	Offset Error, input referred	1x gain, normal mode			-2		mV
		8x gain, normal mode			-5		
		64x gain, normal mode			-4		
	Noise	1x gain, normal mode	V_{CC} = 3.6V Ext. V_{REF}		0.5		mV rms
		8x gain, normal mode			1.5		
		64x gain, normal mode			11		

Note: 1. Maximum numbers are based on characterisation and not tested in production, and valid for 5% to 95% input voltage range.

36.4.7 DAC Characteristics

Table 36-108. Power supply, reference and output range.

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
AV_{CC}	Analog supply voltage		V_{CC}- 0.3		V_{CC}+ 0.3	
AV_{REF}	External reference voltage		1.0		V_{CC}- 0.6	V
$R_{channel}$	DC output impedance				50	Ω
	Linear output voltage range		0.15		AV_{CC}-0.15	V
R_{AREF}	Reference input resistance			>10		MΩ
CAREF	Reference input capacitance	Static load		7		pF
	Minimum Resistance load		1			kΩ
	Maximum capacitance load				100	pF
		1000Ω serial resistance			1	nF
	Output sink/source	Operating within accuracy specification			AV_{CC}/1000	mA
		Safe operation			10	

Table 36-109. Clock and timing.

Symbol	Parameter	Condition		Min.	Typ.	Max.	Units
f_{DAC}	Conversion rate	C_{load}=100pF, maximum step size	Normal mode	0		1000	ksps
			Low power mode	0		500	

36.4.15 SPI Characteristics

Figure 36-26. SPI timing requirements in master mode.

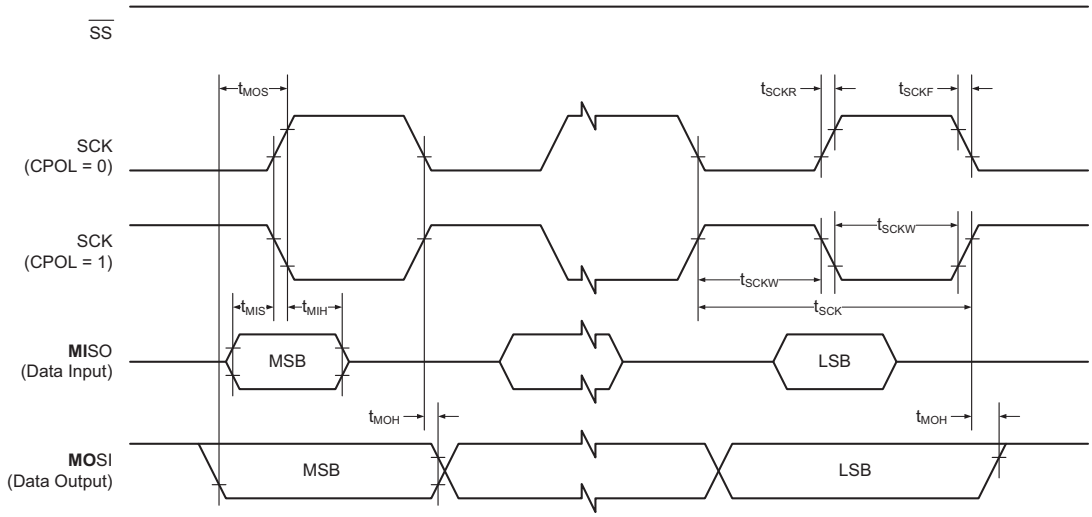
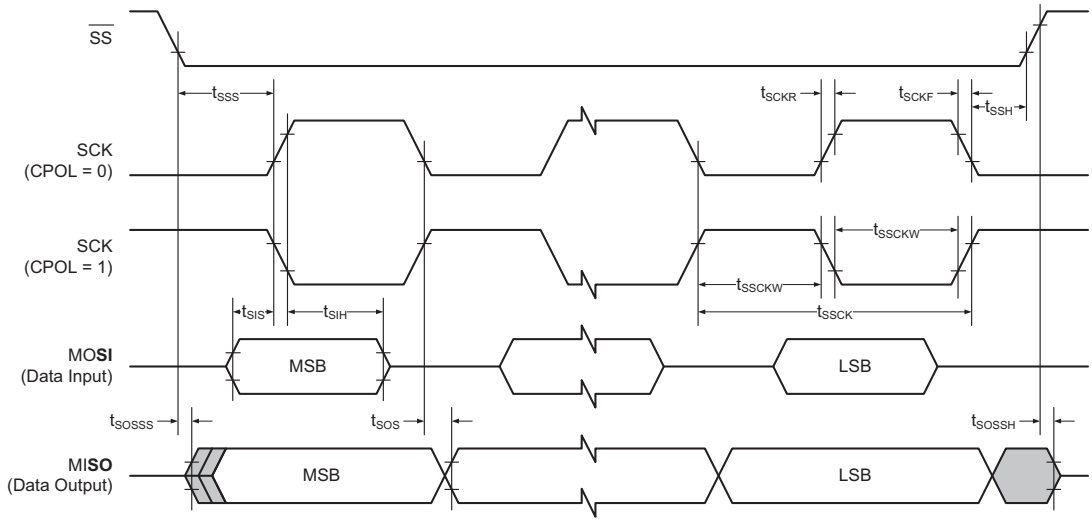


Figure 36-27. SPI timing requirements in slave mode.



37.1.10.4 32MHz Internal Oscillator

Figure 37-74. 32MHz internal oscillator frequency vs. temperature.
DFLL disabled.

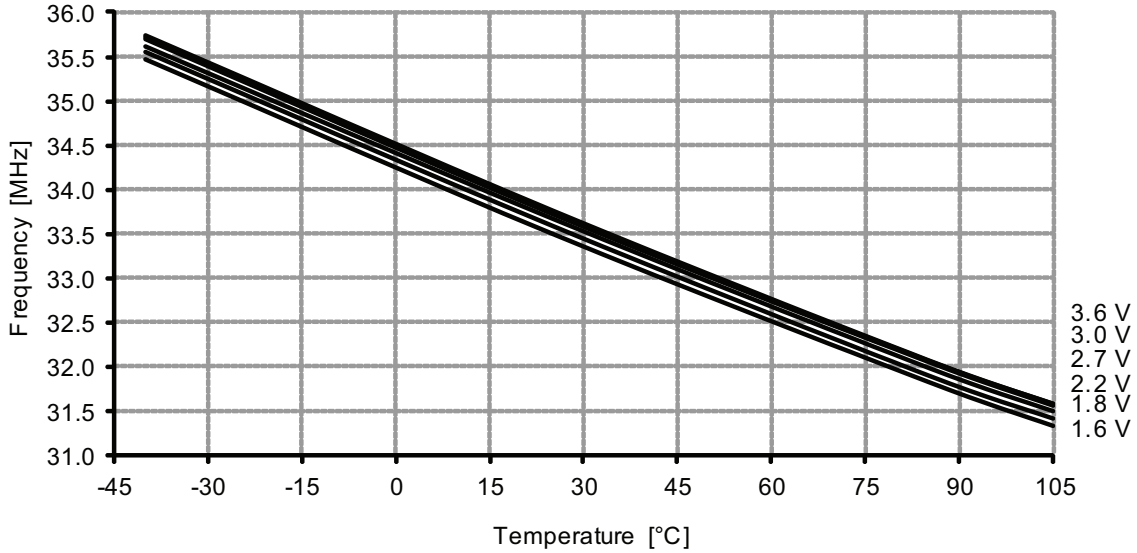
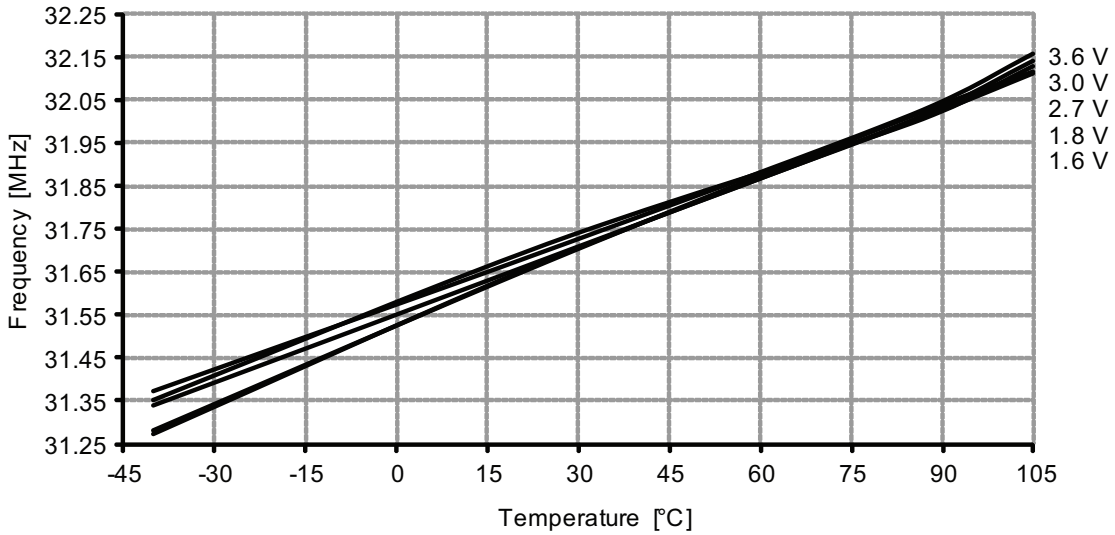


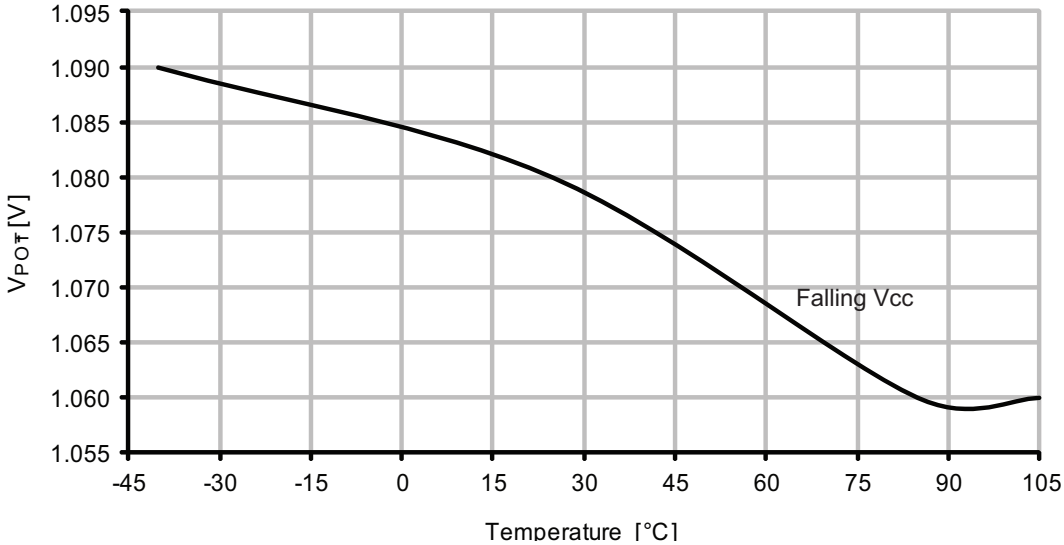
Figure 37-75. 32MHz internal oscillator frequency vs. temperature.
DFLL enabled, from the 32.768kHz internal oscillator.



37.2.9 Power-on Reset Characteristics

Figure 37-150. Power-on reset current consumption vs. V_{CC}.

BOD level = 3.0V, enabled in continuous mode.



37.2.10.4 32MHz Internal Oscillator

Figure 37-157. 32MHz internal oscillator frequency vs. temperature.

DFLL disabled.

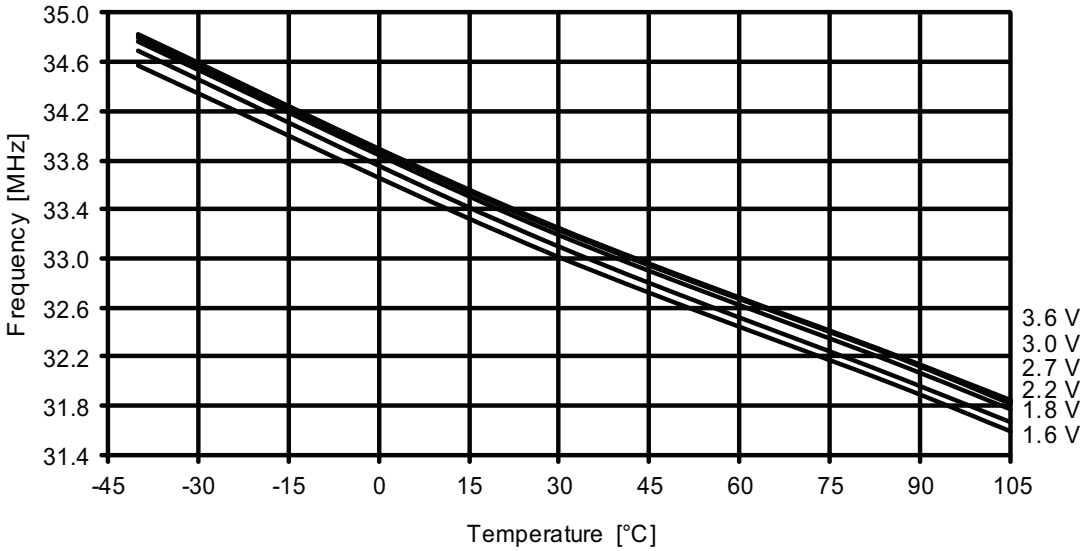


Figure 37-158. 32MHz internal oscillator frequency vs. temperature.

DFLL enabled, from the 32.768kHz internal oscillator.

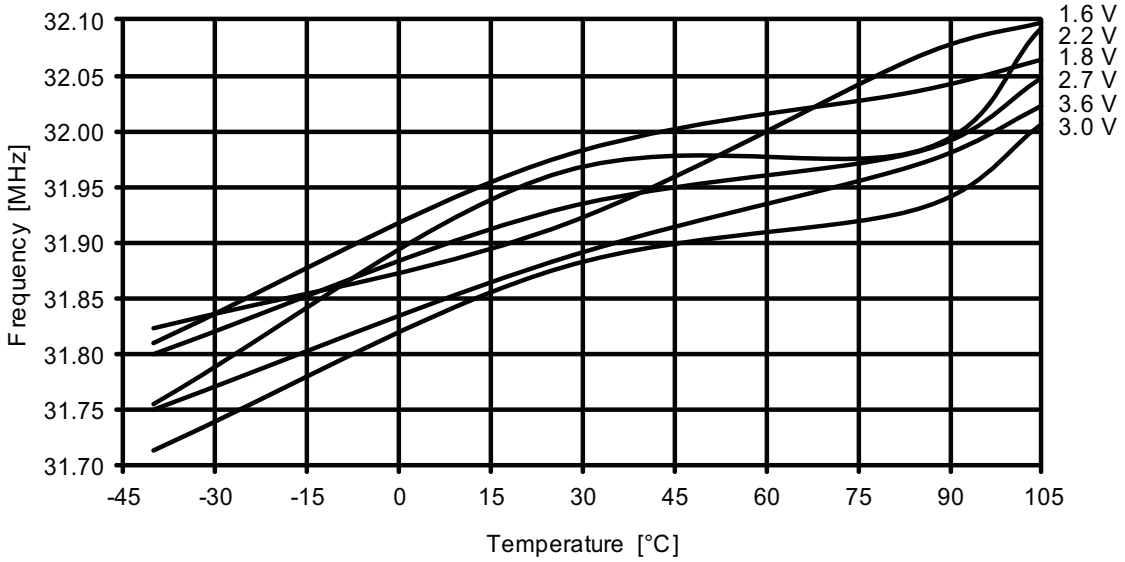
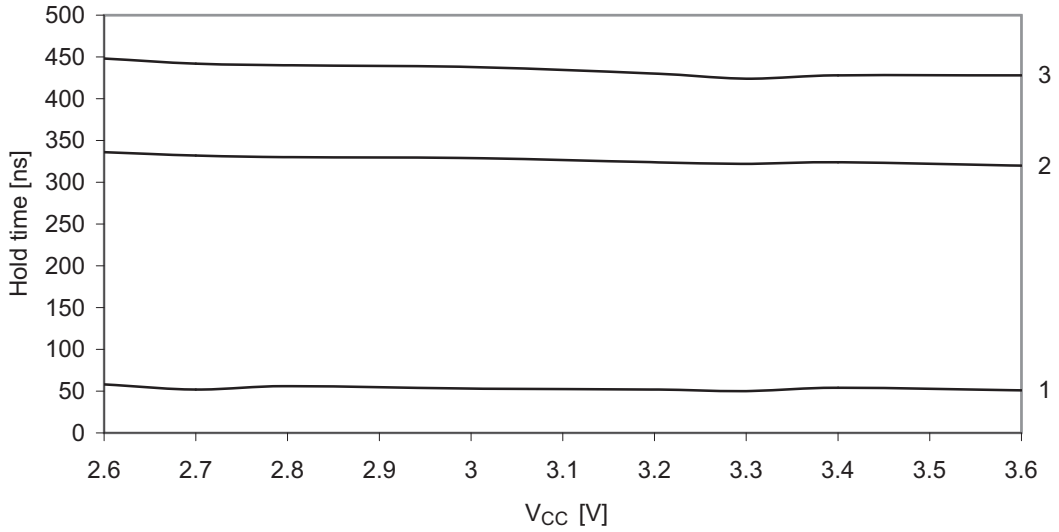


Figure 37-165. SDA hold time vs. supply voltage.



37.2.12 PDI characteristics

Figure 37-166. Maximum PDI frequency vs. V_{CC}.

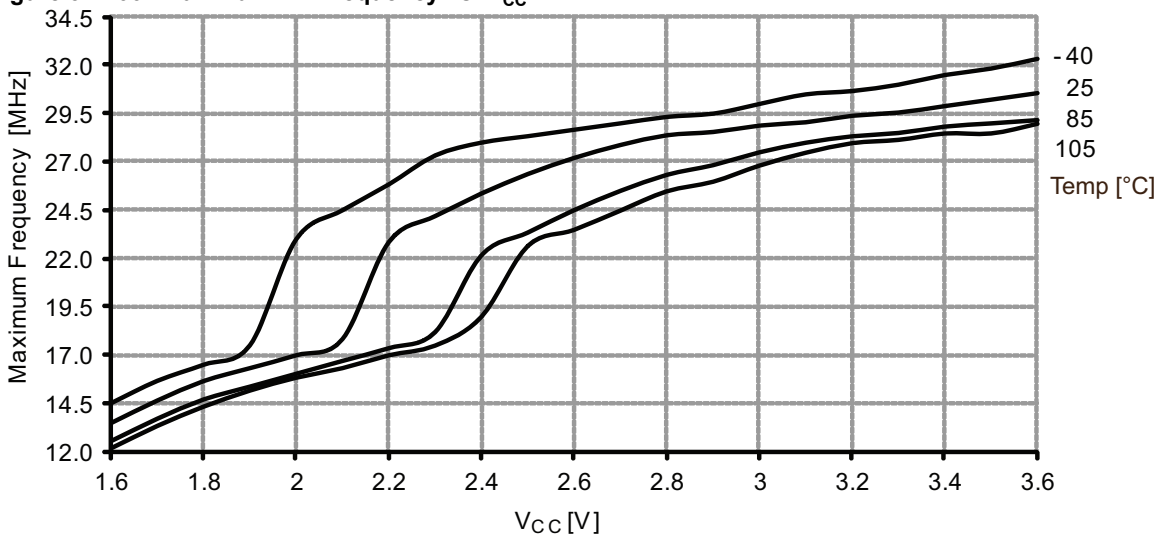


Figure 37-171. Active mode supply current vs. V_{CC}.

f_{SYS} = 2MHz internal oscillator.

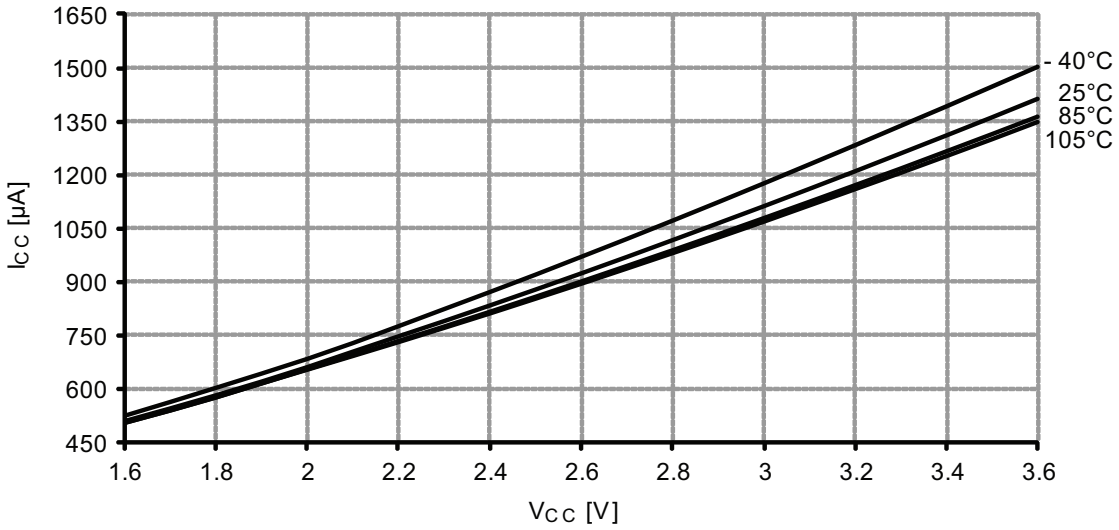


Figure 37-172. Active mode supply current vs. V_{CC}.

f_{SYS} = 32MHz internal oscillator prescaled to 8MHz.

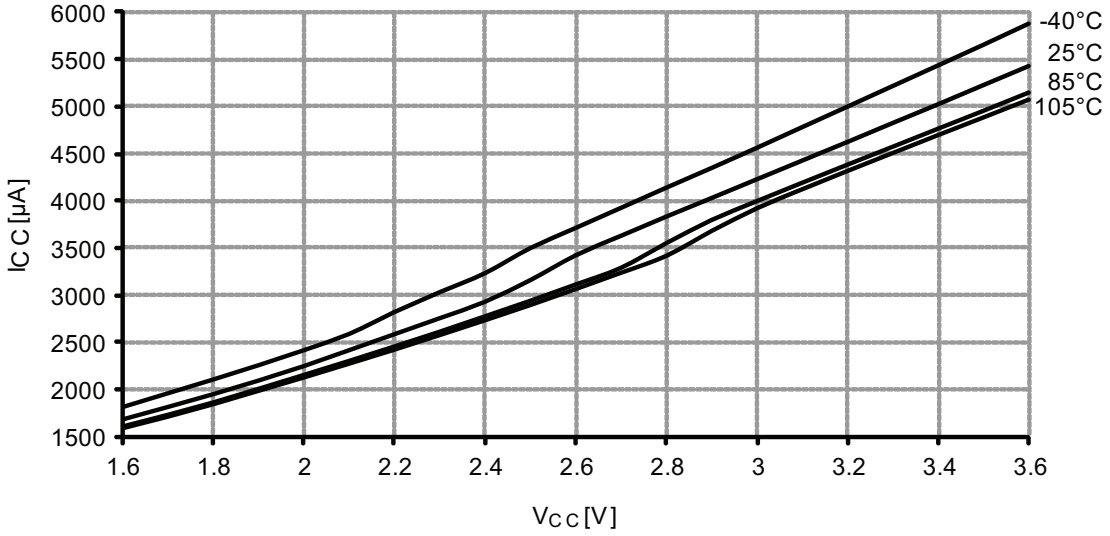


Figure 37-205. DNL error vs. sample rate.

T = 25°C, V_{CC} = 3.6V, V_{REF} = 3.0V external.

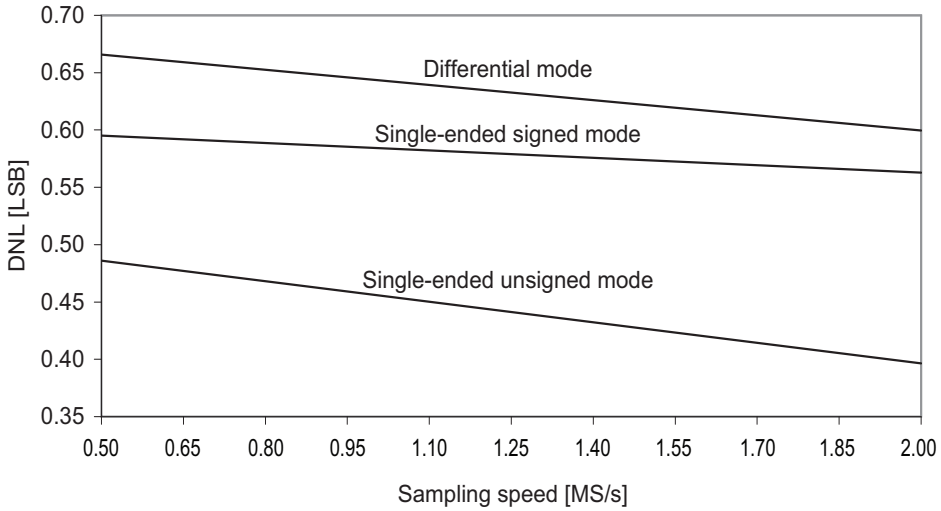


Figure 37-206. DNL error vs. input code.

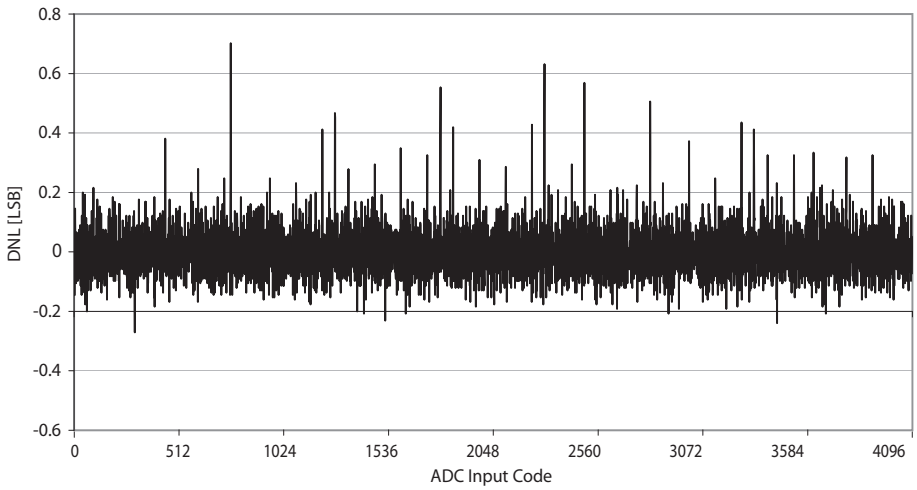


Figure 37-229. Reset pin pull-up resistor current vs. reset pin voltage.
V_{CC} = 3.0V.

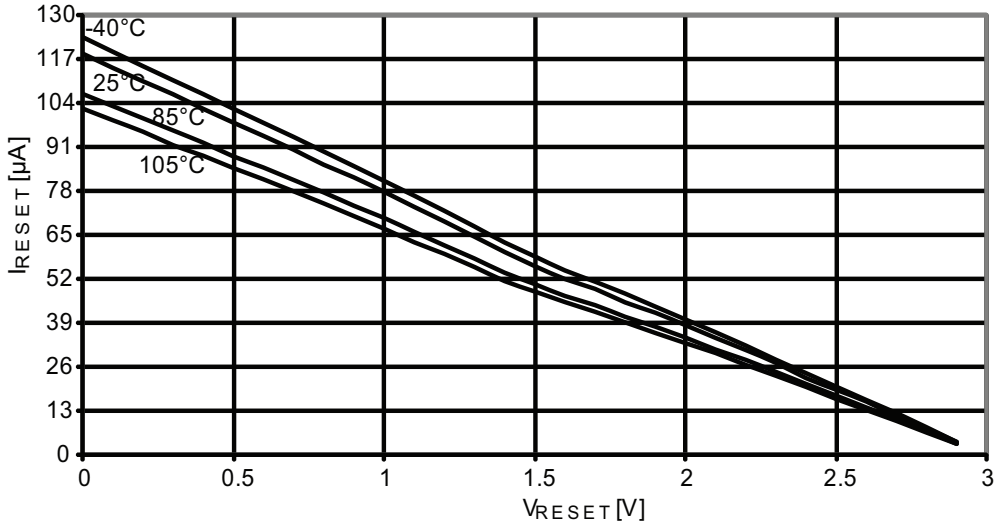


Figure 37-230. Reset pin pull-up resistor current vs. reset pin voltage.
V_{CC} = 3.3V.

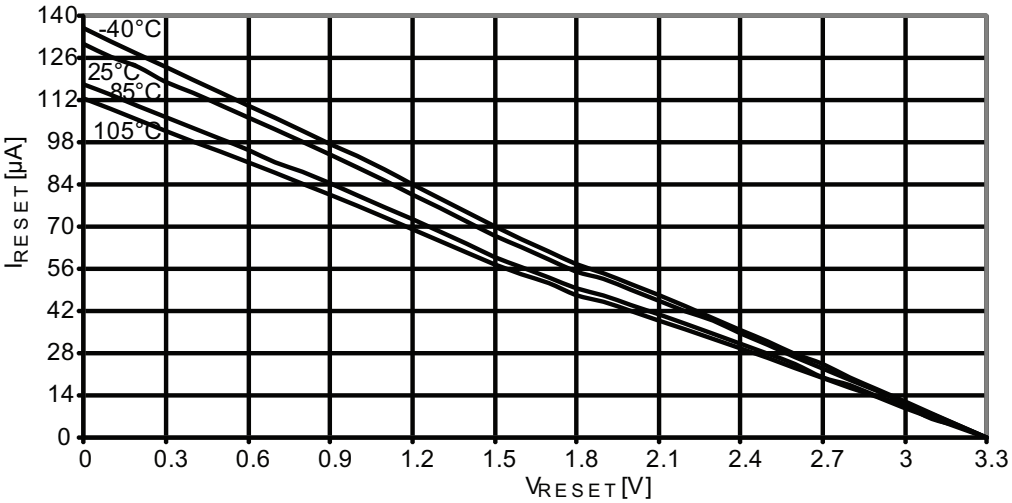


Figure 37-290. Gain error vs. V_{REF}.

T = 25°C, V_{CC} = 3.6V, ADC sampling speed = 500ksps.

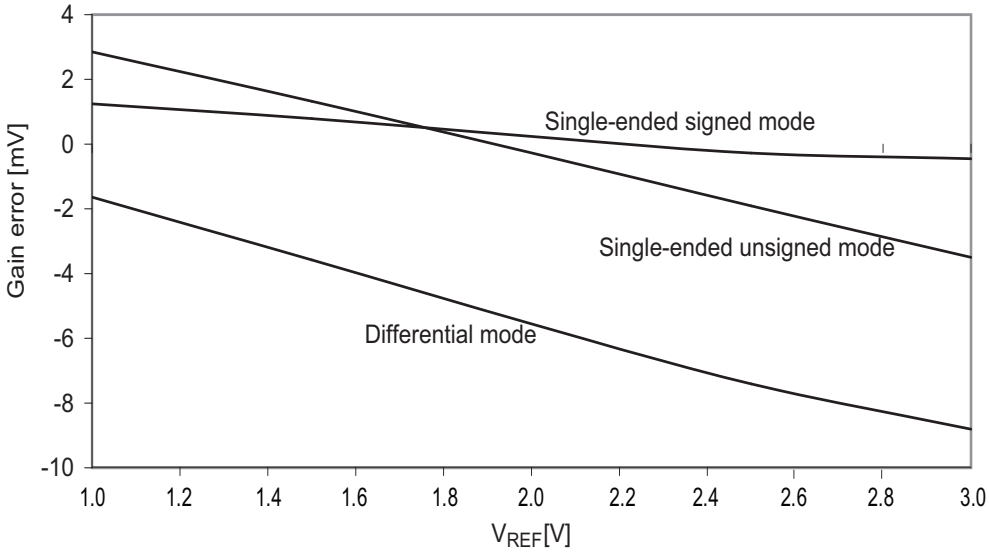


Figure 37-291. Gain error vs. V_{CC}.

T = 25°C, V_{REF} = external 1.0V, ADC sampling speed = 500ksps.

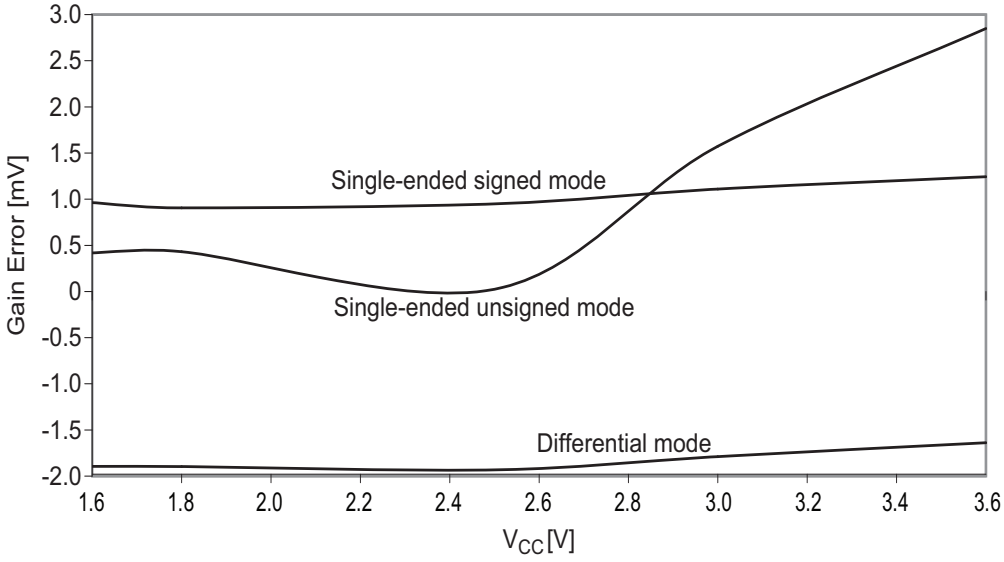


Figure 37-325. 32MHz internal oscillator CALA calibration step size.

V_{CC} = 3.0V.

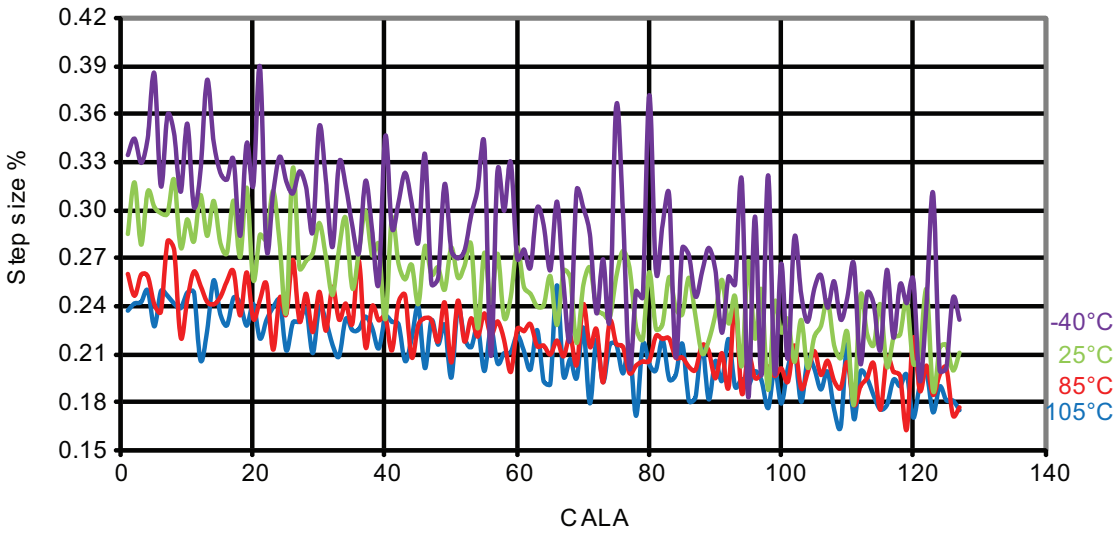
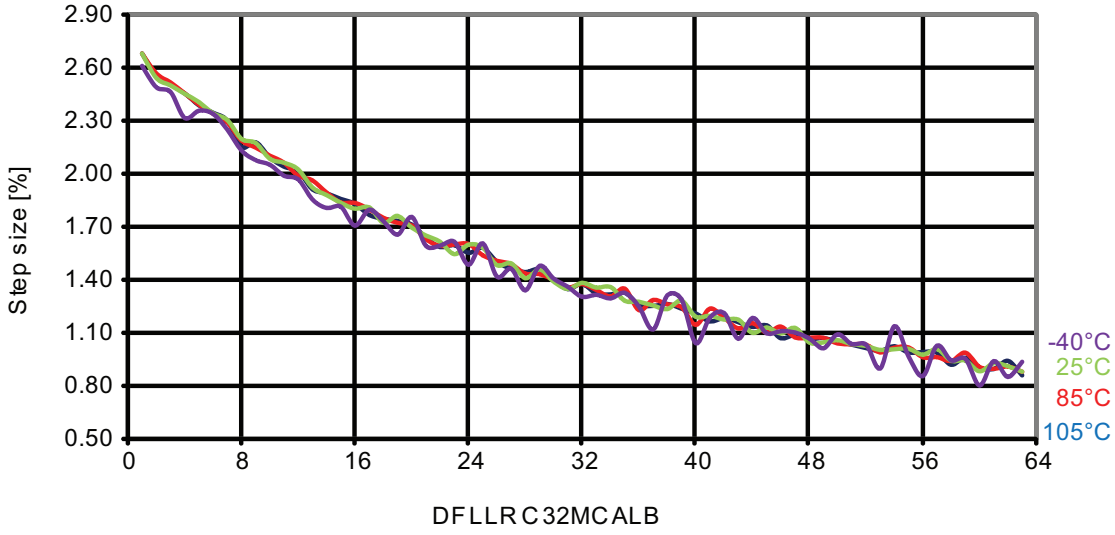


Figure 37-326. 32MHz internal oscillator frequency vs. CALB calibration value.

V_{CC} = 3.0V.